

1. Material Substrate GaAs (N Type)
Epitaxial Layer GaAlAs (P/N Type)

2. Electrode N(Cathode) Side Gold Alloy
P(Anode) Side Gold Alloy

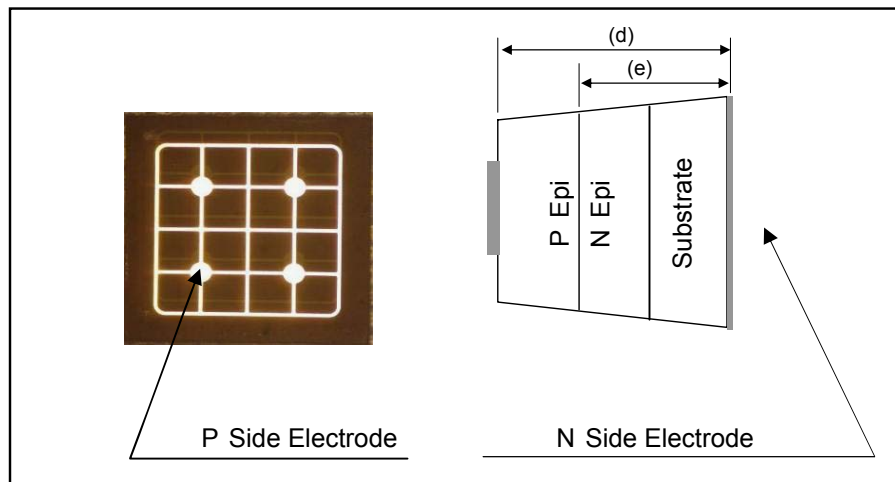
3. Electro-Optical Characteristics

Parameter	Symbo	Min	Typ	Max	Unit	Condition
Forward Voltage	V_F			1.3	V	IF=250mA
Reverse Voltage	V_R	5			V	IR=10uA
Radiant Power	P_O		7		mW	IF=250mA
Wavelength	λ_P		940		nm	IF=20mA
	$\Delta\lambda$		45		nm	IF=20mA

※ Note : LED Chip is mounted on TO-18 gold header without resin coating.

4. Mechanical Data

(a) Emission Area	-----	58.5mil x	58.5mil
(b) Bottom Area	-----	60.0mil x	60.0mil
(c) Bonding Pad	-----	128um	
(d) Chip Thickness	-----	11mil	
(e) Junction Height	-----	6.7mil	



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